

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1-17. (canceled)

1                   18. (previously presented) A method as in claim 24 wherein step (b) advances  
2 curing of the thermosetting resin.

19. (canceled)

1                   20. (previously presented) A method as in claim 24 further comprising a step of  
2 inspecting the semiconductor device.

1                   21. (previously presented) A method as in claim 24 wherein the semiconductor  
2 device comprises an integrated circuit.

1                   22. (previously presented) A method as in claim 24 wherein step (a) includes a  
2 transfer molding process.

1                   23. (previously presented) A method as in claim 24 wherein step (a) includes a  
2 potting process.

1                   24. (Currently amended) A method of making a semiconductor device  
2 comprising:

3                   (a)     sealing the semiconductor device in a package by surrounding it with  
4 thermosetting resin and thermally curing the resin at a first temperature;

5                   (b)     baking the thermosetting resin at a second temperature not higher than the  
6 first temperature, ~~wherein the second temperature is between about 220°C and about 260°C; and;~~

7                   (c) further baking the thermosetting resin at a third temperature higher than  
8   the first temperature, wherein the third temperature is between about 220°C and about 260°C;  
9   and

10               [[c)](d) inspecting the semiconductor device.

1               25. (previously presented) A method as in claim 24 wherein a conductive lead is  
2   adhesively affixed to a main surface of the semiconductor device.

1               26. (previously presented) A method as in claim 25 wherein the conductive lead  
2   is adhesively affixed to a peripheral portion of the main surface of the semiconductor device.

1               27. (previously presented) A method as in claim 26 wherein an electrode of the  
2   semiconductor device is electrically connected to the conductive lead.

28-30 (canceled)